



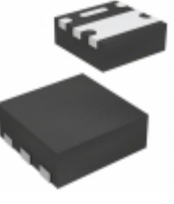

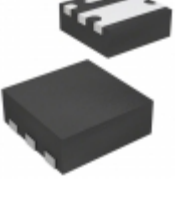
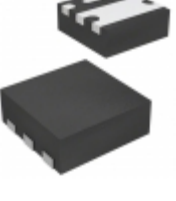

	<h2>SIA408DJ-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIA408DJ-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 30V 4.5A SC70-6</p> <p>Datenblätter:  SIA408DJ-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 18985 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIA408DJ-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 30V 4.5A SC70-6
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	18985 pcs Stock
detaillierte Beschreibung	N-Channel 30V 4.5A (Tc) 3.4W (Ta), 17.9W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SC-70-6
Supplier Device-Gehäuse	PowerPAK® SC-70-6 Single
Verlustleistung (max)	3.4W (Ta), 17.9W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.5A (Tc)
Rds On (Max) @ Id, Vgs	36 mOhm @ 5.3A, 10V
VGS (th) (Max) @ Id	1.6V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	24nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	830pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	2.5V, 10V
Vgs (Max)	±12V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIA408DJ-T1-GE3TR

SIA408DJ-T1-GE3 ist neu im Original, Suche SIA408DJ-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIA408DJ-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIA408DJ-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIA406DJ-T1-GE3 Vishay / Siliconix MOSFET N-CH 12V 4.5A SC-70-6</p>	 <p>SIA406DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 12V 4.5A SC-70-6</p>	 <p>SIA411DJ-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 12A SC70-6</p>	 <p>SIA411DJ-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 12A SC70-6</p>
 <p>SIA402DJ-T1-E3 VISHAY SIA402DJ-T1-E3 VISHAY</p>	 <p>SIA411DJ-T1-E3 Vishay / Siliconix MOSFET P-CH 20V 12A SC70-6</p>	 <p>SIA408DJ-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 4.5A SC70-6</p>	 <p>SIA413ADJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 12A SC70-6</p>

heiße Teile

Mehr

⚙ SIA400EDJ-T1-GE3	➔ SIA400EDJ-T1-GE3	➔ SIA402DJ-T1-E3	D SIA406DJ-T1-GE3	➔ SIA406DJ-T1-GE3
⊣ SIA408DJ-T1-GE3	⚙ SIA411DJ-T1-GE3	D SIA411DJ-T1-GE3	➔ SIA413DJ-T1-GE3	➔ SIA413DJ-T1-GE3
⚙ SIA413DJ-T4-GE3	⊣ SIA414DJ-T1-GE3	⚙ SIA414DJ-T1-GE3	➔ SIA415DJ-T1-GE3	➔ SIA415DJ-T1-GE3
D SIA417DJ-T1-GE3	⚙ SIA417DJ-T1-GE3	⊣ SIA419DJ	⚙ SIA419DJ-T1-GE3	➔ SIA419DJ-T1-GE3
➔ SIA421DJ-T1-GE3	➔ SIA421DJ-T1-GE3	⚙ SIA425EDJ-T1-GE3	⊣ SIA425EDJ-T1-GE3	➔ SIA426DJ-T1-GE3
➔ SIA426DJ-T1-GE3	➔ SIA427DJ-T1-GE3	D SIA427DJ-T1-GE3	⚙ SIA429DJ-T1-GE3	⊣ SIA429DJ-T1-GE3
⚙ SIA430DJ-T1-GE3	D SIA430DJ-T1-GE3	➔ SIA431DJ	➔ SIA431DJ-T1	➔ SIA431DJ-T1-GE3
⊣ SIA431DJ-T1-GE3	⚙ SIA432DJ-T1-GE3	➔ SIA432DJ-T1-GE3	➔ SIA433EDJ	➔ SIA433EDJ-T1-GE3
⚙ SIA433EDJ-T1-GE3	⊣ SIA436DJ-T1-GE3	⚙ SIA436DJ-T1-GE3	D SIA443DJ-T1-GE3	➔ SIA443DJ-T1-GE3
➔ SIA444DJ-T1-GE3	⚙ SIA444DJ-T1-GE3	⊣ SIA445EDJ-T1-GE3	⚙ SIA445EDJ-T1-GE3	➔ SIA447DJ-T1-GE3

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